

## NTE2507 Silicon NPN Transistor High Frequency Video Output

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector-Base Voltage, $V_{CB0}$ .....	200V
Collector-Emitter Voltage, $V_{CEO}$ .....	200V
Emitter-Base Voltage, $V_{EBO}$ .....	5V
Collector Current, $I_C$ .....	400mA
Collector Power Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_C$ .....	20W
Operating Junction Temperature, $T_J$ .....	+150°C

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 150V$	-	-	0.1	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 10V, I_C = 50\text{mA}$	40	-	320	
Transition Frequency	$f_T$	$V_{CE} = 30V, I_C = 100\text{mA}$	-	400	-	MHz
Output Capacitance	$C_{ob}$		-	4.2	-	pF

